

2SC4132 / 2SD1857 / 2SD2343

- 1) High breakdown voltage. ($V_{CEO} = 120V$)
- 2) Low collector output capacitance.
(Typ. 20pF at $V_{CB} = 10V$)
- 3) High transition frequency. ($f_T = 80MHz$)
- 4) Complements the 2SB1236.

Parameter		Symbol	Limits	Unit
Collector-base voltage		V_{CB0}	120	V
Collector-emitter voltage		V_{CE0}	120	V
Emitter-base voltage		V_{EB0}	5	V
Collector current		I_C	2	A
		I_{CP}	3	A ^{*1}
Collector power dissipation	2SC4132	P_C	0.5	W ^{*2}
			2	
			1	
			1.5	
	2SD2343		5	W (T _c = 25°C)
Junction temperature		T _J	150	°C
Storage temperature		T _{stg}	-55~+150	°C

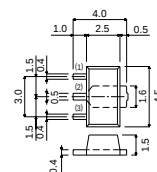
*1 Single pulse Pw = 10ms

*2 When mounted on a 40 × 40 × 0.7mm ceramic board.

Type	2SC4132	2SD1857	2SD2343
Package	MPT3	ATV	TO-126FP
hFE	PQR	PQR	PQ
Marking	CB [★]	—	—
Code	T100	TV2	—
Basic ordering unit (pieces)	1000	2500	1000

* Denotes h_{EE}

2SC4132



ROHM : MPT3
EIAJ : SC-62

- (1) Base(Gate)
- (2) Collector(Drain)
- (3) Emitter(Source)

Taping specifications

ROHM : ATV

- (1) Emitter
- (2) Collector
- (3) Base

ROHM : TO-126FP

- (1) Emitter
- (2) Collector
- (3) Base

Parameter		Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage		BV _{CBO}	120	–	–	V	I _C = 50μA
Collector-emitter breakdown voltage		BV _{CEO}	120	–	–	V	I _C = 1mA
Emitter-base breakdown voltage		BV _{EB0}	5	–	–	V	I _E = 50μA
Collector cutoff current		I _{CBO}	–	–	1	μA	V _{CB} = 100V
Emitter cutoff current		I _{EB0}	–	–	1	μA	V _{EB} = 4V
Collector-emitter saturation voltage		V _{CE(sat)}	–	–	0.4	V	I _C /I _B = 1A/0.1A
DC current transfer ratio	2SC4132,2SD1857	h _{FE}	82	–	390	–	V _{CE} /I _C = 5V/0.1A
	2SD2343		82	–	270	–	
Transition frequency		f _T	–	80	–	MHz	V _{CE} = 5V , I _E = –0.1A , f = 30MHz
Output capacitance		C _{ob}	–	20	–	pF	V _{CB} = 10V , I _E = 0A , f = 1MHz

* Measured using pulse current.